Littelfuse
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Power Module
1700V 100A IGBT Module

MG17100S-BN4MM

RoHS

Features

- IGBT³ CHIP(1700V Trench+Field Stop technology)
- Low turn-off losses, short tail current
- $V_{CE(sat)}$ with positive temperature coefficient
- DIODE CHIP(1700V EMCON 3 technology)
- Free wheeling diodes with fast and soft reverse recovery

Applications

- High frequency switching application
- Medical applications
- Motion/servo control
- UPS systems

Agency Approvals

AGENCY	AGENCY FILE NUMBER
	E71639

Module Characteristics (T_c = 25°C, unless otherwise specified)

Symbol	Parameters	Test Conditions	Min	Typ	Max	Unit
$T_{J\ max)}$	Max. Junction Temperature				150	°C
$T_{J\ op}$	Operating Temperature		-40		125	°C
T_{stg}	Storage Temperature		-40		125	°C
V_{isol}	Insulation Test Voltage	AC, t=1min		4000		V
CTI	Comparative Tracking Index		350			
Torque	Module-to-Sink	Recommended (M6)	3		5	N·m
Torque	Module Electrodes	Recommended (M5)	2.5		5	N·m
Weight				160		g

Absolute Maximum Ratings (T_c = 25°C, unless otherwise specified)

Symbol	Parameters	Test Conditions	Values	Unit
IGBT				
V_{CES}	Collector - Emitter Voltage	T_J=25°C	1700	V
V_{GES}	Gate - Emitter Voltage		±20	V
I_C	DC Collector Current	T_C=25°C	150	A
		T_C=80°C	100	A
I_{CM}	Repetitive Peak Collector Current	t_P=1ms	200	A
P_{tot}	Power Dissipation Per IGBT		620	W
Diode				
V_{RRM}	Repetitive Reverse Voltage	T_J=25°C	1700	V
$I_{F(AV)}$	Average Forward Current	T_C=25°C	150	A
		T_C=80°C	100	A
I_{FRM}	Repetitive Peak Forward Current	t_P=1ms	200	A
I^2t		T_J =125°C, t=10ms, V_R=0V	1800	A^2S

Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

Revised:05/19/15

Electrical and Thermal Specifications (T_c = 25°C, unless otherwise specified)

Symbol	Parameters	Test Conditions		Min	Typ	Max	Unit
IGBT							
$V_{GE(th)}$	Gate - Emitter Threshold Voltage	$V_{CE}=V_{GE}$, I_C=4.0mA		5.2	5.8	6.4	V
$V_{CE(sat)}$	Collector - Emitter Saturation Voltage	I_C=100A, V_{GE}=15V, T_J=25°C			2.0	2.45	V
		I_C=100A, V_{GE}=15V, T_J=125°C			2.4		V
I_{CES}	Collector Leakage Current	V_{CE}=1700V, V_{GE}=0V, T_J=25°C				3	mA
		V_{CE}=1700V, V_{GE}=0V, T_J=125°C				20	mA
I_{GES}	Gate Leakage Current	V_{CE}=0V, V_{GE}=±20V, T_J=125°C		-400		400	nA
R_{Gint}	Intergrated Gate Resistor				7.5		Ω
Q_{ge}	Gate Charge	V_{CE}=900V, I_C=100A , V_{GE}=±15V			1.2		μC
C_{ies}	Input Capacitance	V_{CE}=25V, V_{GE}=0V, f =1MHz			9		nF
C_{res}	Reverse Transfer Capacitance				0.29		nF
$t_{d(on)}$	Turn - on Delay Time	V_{CC}=900V I_C=100A R_G =4Ω V_{GE}=±15V Inductive Load	T_J =25°C		370		ns
			T_J =125°C		400		ns
t_r	Rise Time		T_J =25°C		40		ns
			T_J =125°C		50		ns
$t_{d(off)}$	Turn - off Delay Time		T_J =25°C		650		ns
			T_J =125°C		800		ns
t_f	Fall Time		T_J =25°C		180		ns
			T_J =125°C		300		ns
E_{on}	Turn - on Energy		T_J =25°C		22		mJ
			T_J =125°C		32		mJ
E_{off}	Turn - off Energy		T_J =25°C		21.5		mJ
			T_J =125°C		32.5		mJ
I_{SC}	Short Circuit Current	t_{psc}≤10μS , V_{GE}=15V; T_J=125°C, V_{CC}=1000V			400		A
R_{thJC}	Junction-to-Case Thermal Resistance (Per IGBT)					0.20	K/W
Diode							
V_F	Forward Voltage	I_F=100A , V_{GE}=0V, T_J =25°C			1.8	2.2	V
		I_F=100A , V_{GE}=0V, T_J =125°C			1.9		V
I_{RRM}	Max. Reverse Recovery Current	I_F=100A , V_R=900V			165		A
Q_{rr}	Reverse Recovery Charge	di_F/dt=-2450A/μs			48.5		μC
E_{rec}	Reverse Recovery Energy	T_J=125°C			27.5		mJ
R_{thJCD}	Junction-to-Case Thermal Resistance (Per Diode)					0.36	K/W

Figure 1: Typical Output Characteristics

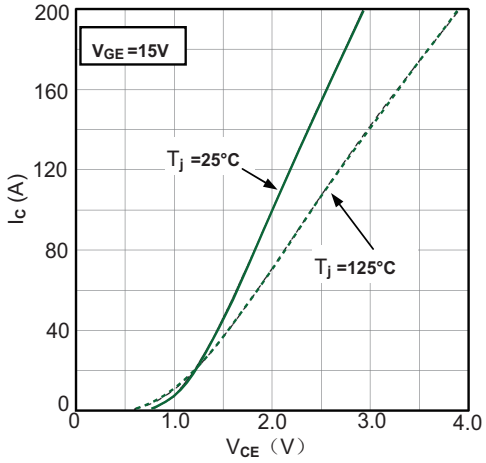


Figure 2: Typical Output Characteristics

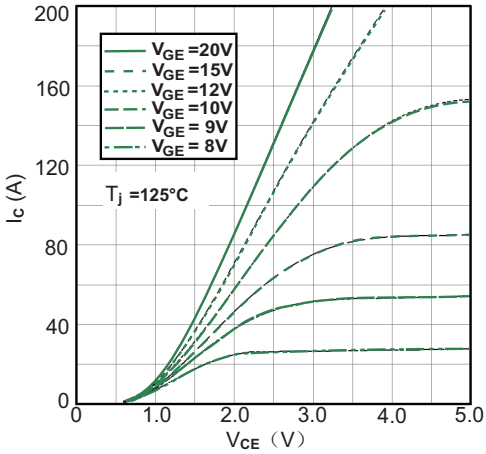


Figure 3: Typical Transfer characteristics

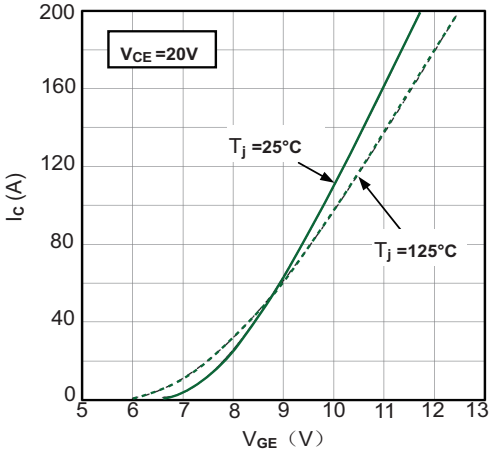


Figure 4: Switching Energy vs. Gate Resistor

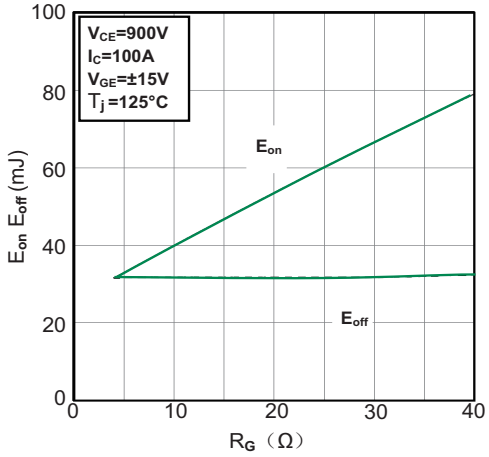


Figure 5: Switching Energy vs. Collector Current

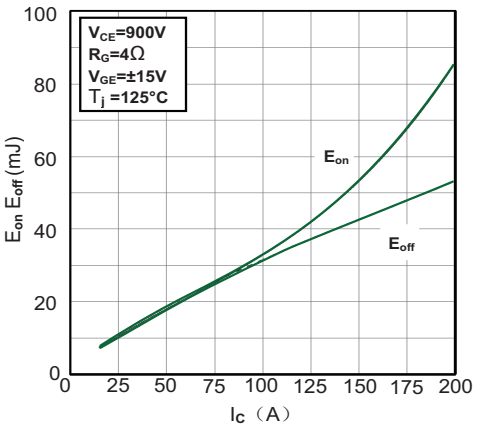


Figure 6: Reverse Biased Safe Operating Area

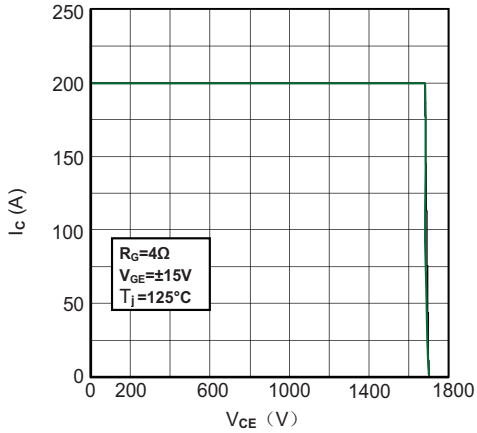


Figure 7: Diode Forward Characteristics

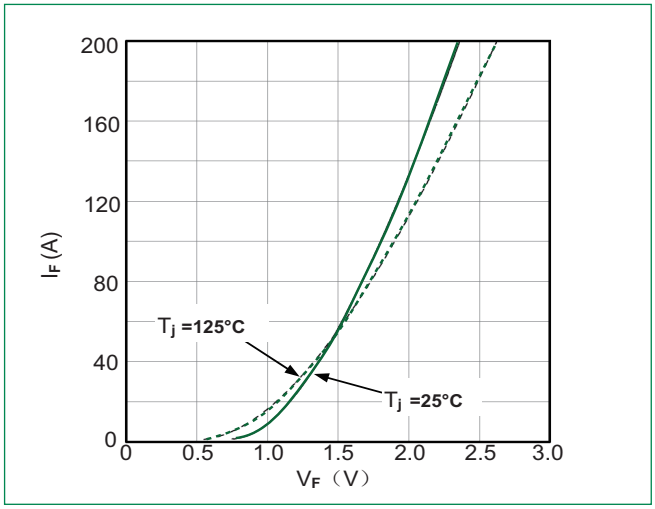


Figure 8: Switching Energy vs. Gate Resistor

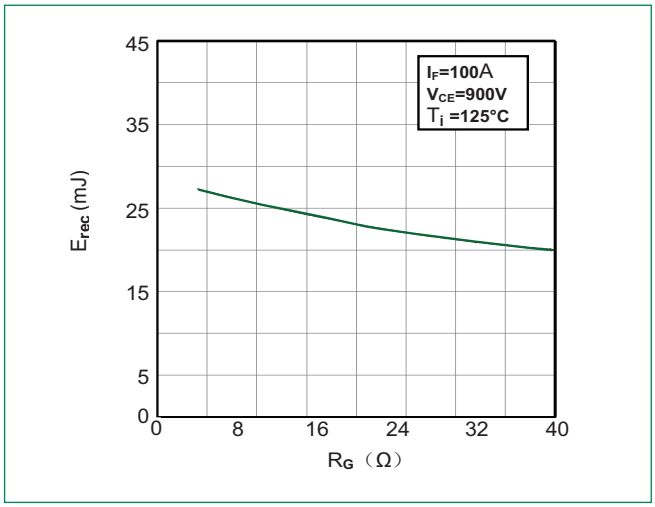


Figure 9: Switching Energy vs. Forward Current

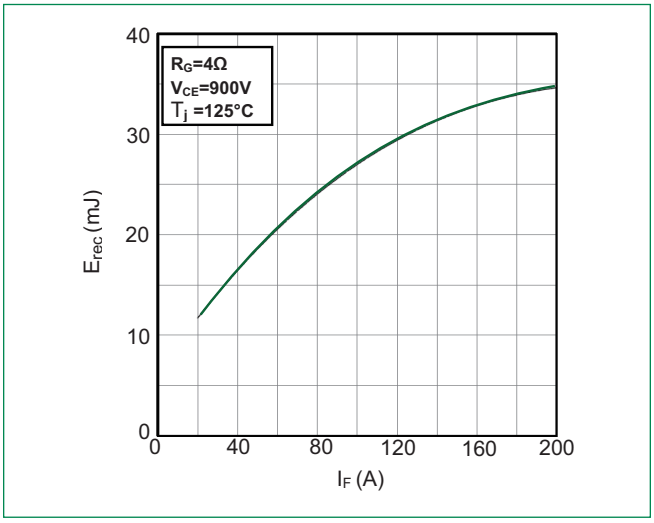
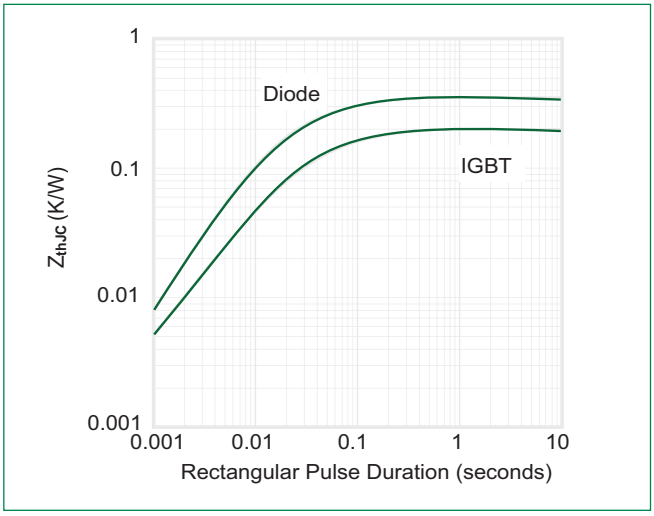


Figure 10: Transient Thermal Impedance of Diode and IGBT



Power Module
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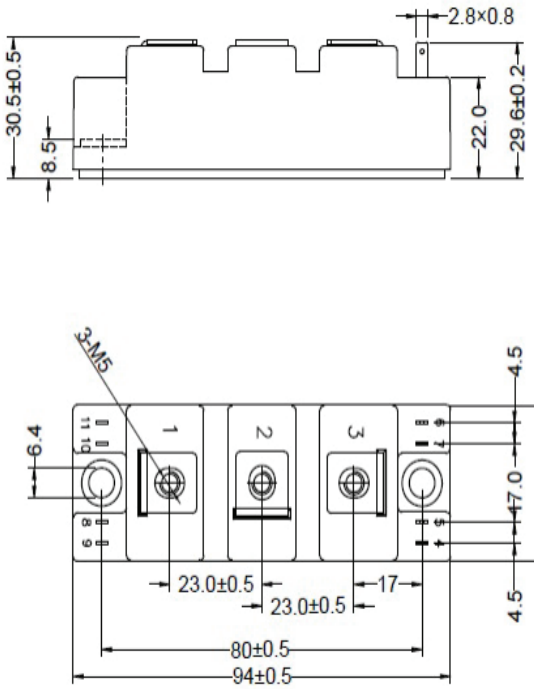
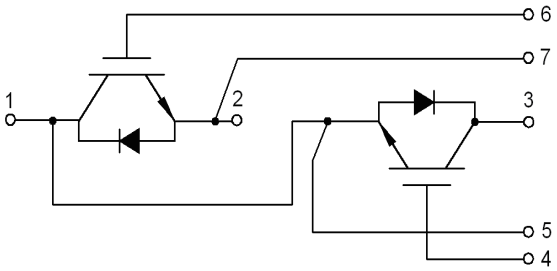
Dimensions-Package S



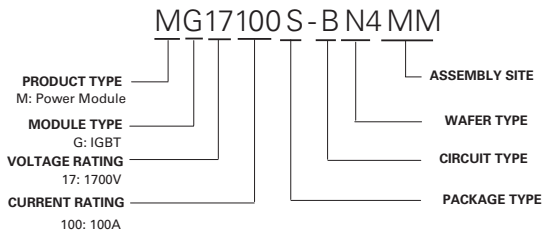
Circuit Diagram



Packing Options

Part Number	Marking	Weight	Packing Mode	M.O.Q
MG17100S-BN4MM	MG17100S-BN4MM	160g	Bulk Pack	50

Part Numbering System



Part Marking System